50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

14 September 2018

Product data sheet

1. General description

NPN/PNP Resistor-Equipped double Transistors (RET) in a leadless ultra small DFN1412-6 (SOT1268) leadless Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PRMH11; PNP/PNP complement: PRMB11.

2. Features and benefits

- 100 mA output current capability
- · Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Low package height of 0.5 mm
- AEC-Q101 qualified

3. Applications

- · Digital applications
- Cost-saving alternative to BC847/BC857 series in digital applications
- Control of IC inputs
- Switching loads

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit | |
|------------------|---|--|-----|-----|-----|-----|------|--|
| Per transistor, | Per transistor, for the PNP transistor with negative polarity | | | | | | | |
| V _{CEO} | collector-emitter voltage | open base | | - | - | 50 | V | |
| Io | output current | | | - | - | 100 | mA | |
| h _{FE} | DC current gain | V _{CE} = 5 V; I _C = 5 mA; T _{amb} = 25 °C | | 30 | - | - | | |
| R1 | bias resistor 1 | T _{amb} = 25 °C | [1] | 7 | 10 | 13 | kΩ | |
| R2/R1 | bias resistor ratio | | [1] | 0.8 | 1 | 1.2 | | |

[1] See section "Test information" for resistor calculation and test conditions.



50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|------------------------|------------------------|--------------------------|
| 1 | GND1 | GND (emitter) TR1 | | O1 I2 GND2 |
| 2 | l1 | input (base) TR1 | 1 7 6 | |
| 3 | O2 | output (collector) TR2 | 2 5 | R1 R2 |
| 4 | GND2 | GND (emitter) TR2 | | TR2 |
| 5 | 12 | input (base) TR2 | 3 8 4 | TR1 R2 R1 |
| 6 | O1 | output (collector) TR1 | | |
| 7 | O1 | output (collector) TR1 | Transparent top view | 0.000 |
| 8 | O2 | output (collector) TR2 | DFN1412-6 (SOT1268) | GND1 I1 O2 aaa-007379 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | age | | | | | |
|-------------|---------|---|---------|--|--|--|--|
| | Name | Description | Version | | | | |
| PRMD3 | | plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm | SOT1268 | | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PRMD3 | B3 |

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

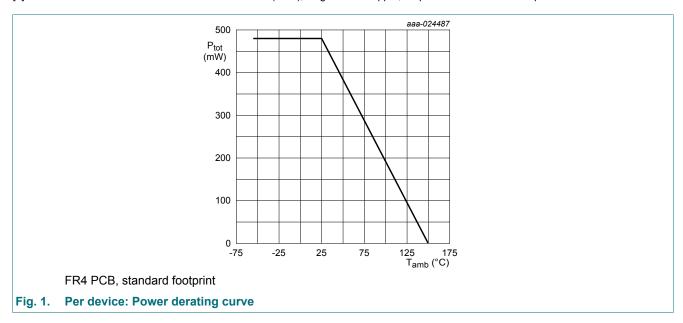
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|--------------------------------|--------------------------|-----|-----|-----|------|
| Per transist | or, for the PNP transistor wit | n negative polarity | | | | |
| V _{CBO} | collector-base voltage | open emitter | | - | 50 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | 50 | V |
| V_{EBO} | emitter-base voltage | open collector | | - | 10 | V |
| VI | input voltage | positive | | - | 40 | V |
| | | negative | | - | -10 | V |
| Io | output current | | | - | 100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 325 | mW |
| Per device | | | | | | |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 480 | mW |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------|---|-------------|-----|-----|-----|-----|------|
| Per transistor | | | | | | | |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] | - | - | 385 | K/W |
| Per device | Per device | | | | | | |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] | - | - | 261 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

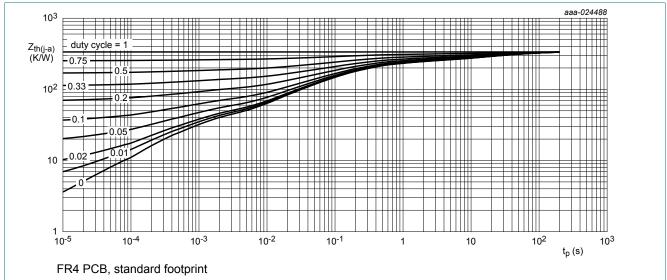


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------|--------------------------------------|--|-----|-----|-----|-----|------|
| Per transist | or, for the PNP transistor v | vith negative polarity | | | | | |
| I _{CEO} | | V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C | | - | - | 1 | μΑ |
| | current | V _{CE} = 30 V; I _B = 0 A; T _{amb} = 150 °C | | - | - | 5 | μΑ |
| I _{CBO} | collector-base cut-off current | V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C | | - | - | 100 | nA |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ | | - | - | 400 | μA |
| h _{FE} | DC current gain | V _{CE} = 5 V; I _C = 5 mA; T _{amb} = 25 °C | | 30 | - | - | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$ | | - | - | 150 | mV |
| V _{I(off)} | off-state input voltage | V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C | | - | 1.1 | 0.8 | V |
| V _{I(on)} | on-state input voltage | V_{CE} = 0.3 V; I_{C} = 10 mA; T_{amb} = 25 °C | | 2.5 | 1.8 | - | V |
| R1 | bias resistor 1 | T _{amb} = 25 °C | [1] | 7 | 10 | 13 | kΩ |
| R2/R1 | bias resistor ratio | | [1] | 0.8 | 1 | 1.2 | |
| C _C | collector capacitance | V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C | | - | - | 2.5 | pF |
| | | V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C | | - | - | 3 | pF |
| f _T | transition frequency | V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C | [2] | - | 230 | - | MHz |
| | | V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C | [2] | - | 180 | - | MHz |

- [1] See section "Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor.

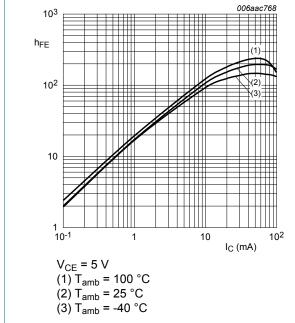


Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values

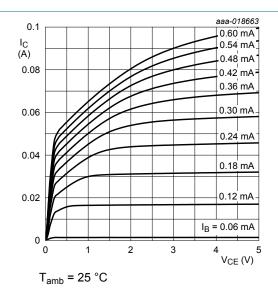
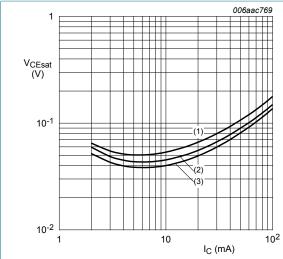


Fig. 4. NPN transistor: Collector current as a function of collector-emitter voltage; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

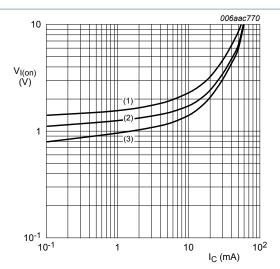


$$I_{\rm C}/I_{\rm B} = 20$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 5. **NPN** transistor: Collector-emitter saturation voltage as a function of collector current; typical values

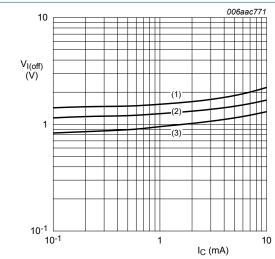


$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

NPN transistor: On-state input voltage as a Fig. 6. function of collector current; typical values



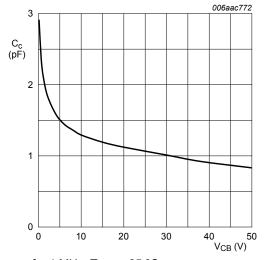
$$V_{CE} = 5 V$$

$$(1) T_{amb} = -40 °C$$

$$(2) T_{amb} = 25 °C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

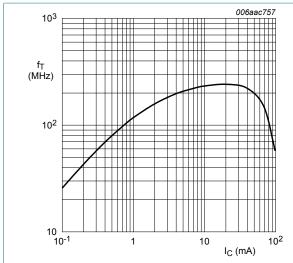
Fig. 7. NPN transistor: Off-state input voltage as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

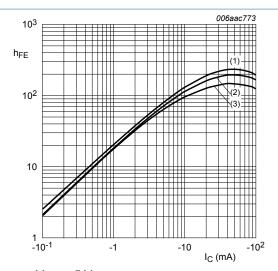
Fig. 8. NPN transistor: Collector capacitance as a function of collector-base voltage; typical

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)



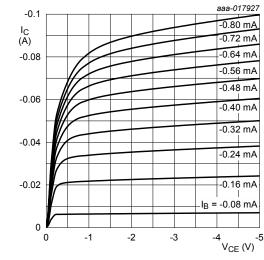
 V_{CE} = 5 V; T_{amb} = 25 °C

Fig. 9. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



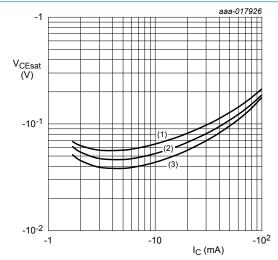
V_{CE} = -5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 20$

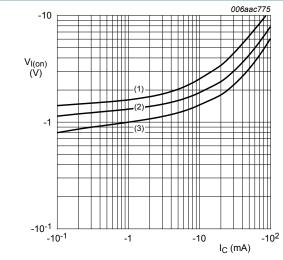
(1) T_{amb} = 100 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 12. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)



 V_{CE} = -0.3 V

(1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 13. PNP transistor: On-state input voltage as a function of collector current; typical values

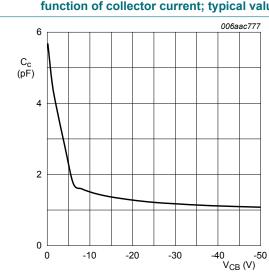
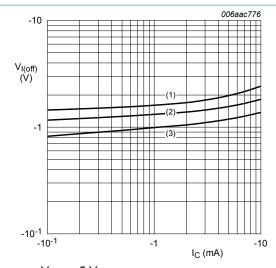


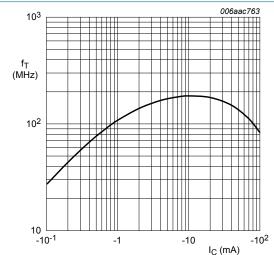
Fig. 15. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values

 $f = 1 MHz; T_{amb} = 25 °C$



V_{CE} = -5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 14. PNP transistor: Off-state input voltage as a function of collector current; typical values



 V_{CE} = -5 V; T_{amb} = 25 °C

Fig. 16. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Resistor calculation

Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

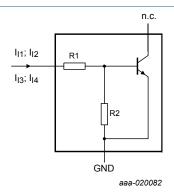


Fig. 17. NPN transistor: Resistor test circuit

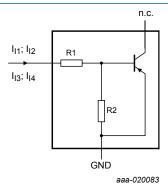


Fig. 18. PNP transistor: Resistor test circuit

Resistor test conditions

Table 8. Resistor test conditions

Per transistor; for the PNP transistor with negative polarity

| R1 (kΩ) | R2 (kΩ) | Test conditions | st conditions | | | | | |
|---------|---------|-----------------|-----------------|-----------------|-----------------|--|--|--|
| | | I _{I1} | I ₁₂ | I ₁₃ | I ₁₄ | | | |
| 10 | 10 | 350 μΑ | 450 μA | -350 µA | -450 μA | | | |

PRMD3

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

12. Package outline

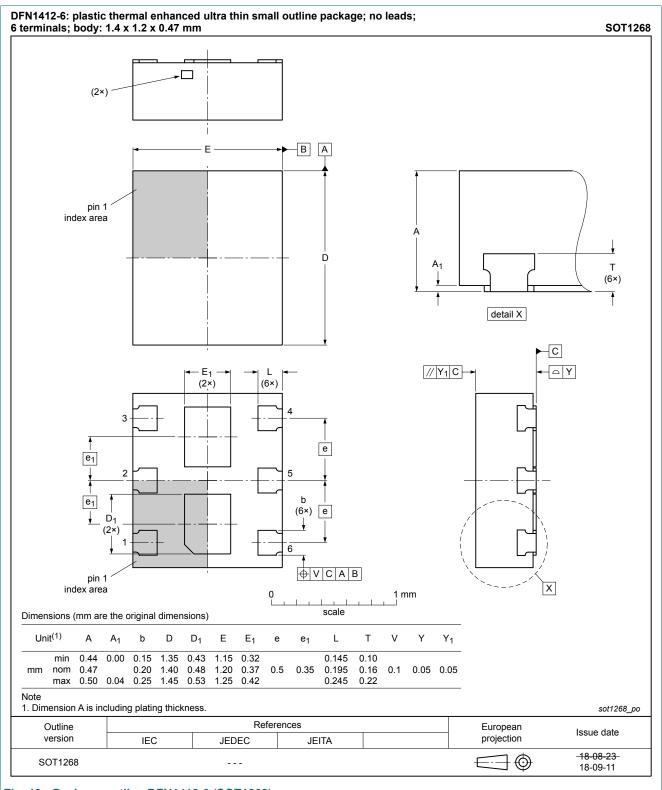
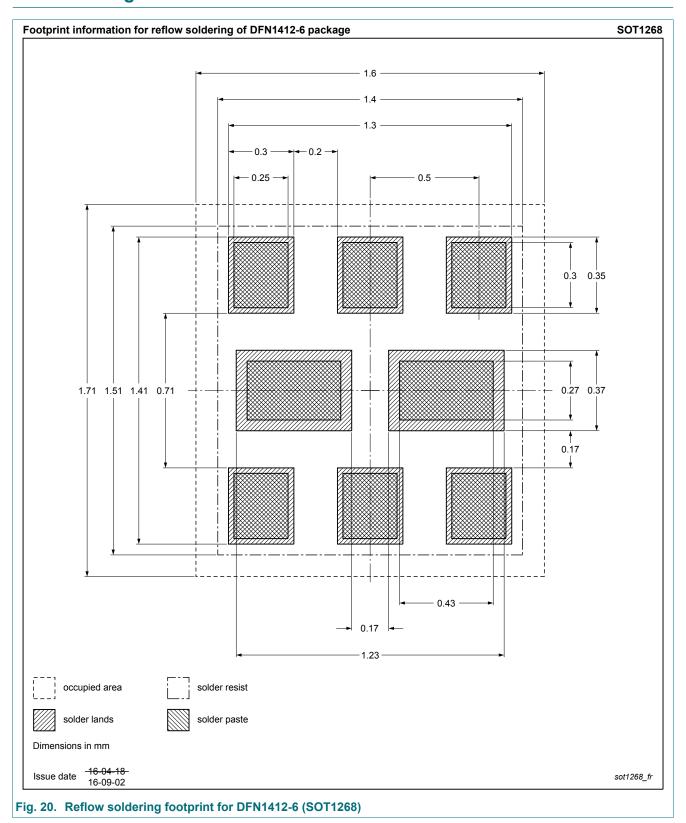


Fig. 19. Package outline DFN1412-6 (SOT1268)

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

13. Soldering



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14. Revision history

Table 9. Revision history

| · · · · · · · · · · · · · · · · · · · | | | | | | | |
|---------------------------------------|----------------------|---|---------------|------------|--|--|--|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | | |
| PRMD3 v.2 | 20180914 | Product data sheet | - | PRMD3 v.1 | | | |
| Modifications: | Package outline draw | Package outline drawing updated: Unit T added | | | | | |
| PRMD3 v.1 | 20170615 | Product data sheet | - | - | | | |

12 / 14

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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PRMD3

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

Contents

| 1. | General description | 1 |
|-----|-------------------------|-----|
| 2. | Features and benefits | 1 |
| 3. | Applications | 1 |
| 4. | Quick reference data | 1 |
| 5. | Pinning information | 2 |
| 6. | Ordering information | 2 |
| 7. | Marking | 2 |
| 8. | Limiting values | 3 |
| 9. | Thermal characteristics | 4 |
| 10. | . Characteristics | 5 |
| 11. | Test information | 9 |
| 12. | Package outline | 10 |
| 13. | Soldering | 11 |
| 14. | . Revision history | .12 |
| | Legal information | |
| | | |

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